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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

E·XFI

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	119
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1afs1500-2fg256i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

The NGMUX macro is simplified to show the two clock options that have been selected by the GLMUXCFG[1:0] bits. Figure 2-25 illustrates the NGMUX macro. During design, the two clock sources are connected to CLK0 and CLK1 and are controlled by GLMUXSEL[1:0] to determine which signal is to be passed through the MUX.



Figure 2-25 • NGMUX Macro

The sequence of switching between two clock sources (from CLK0 to CLK1) is as follows (Figure 2-26):

- GLMUXSEL[1:0] transitions to initiate a switch.
- GL drives one last complete CLK0 positive pulse (i.e., one rising edge followed by one falling edge).
- From that point, GL stays Low until the second rising edge of CLK1 occurs.
- At the second CLK1 rising edge, GL will begin to continuously deliver the CLK1 signal.
- Minimum t_{sw} = 0.05 ns at 25°C (typical conditions)

For examples of NGMUX operation, refer to the Fusion FPGA Fabric User Guide.



Figure 2-26 • NGMUX Waveform



RAM512X18 Description

Figure 2-49 • RAM512X18

ESTOP, FSTOP

ESTOP is used to stop the FIFO read counter from further counting once the FIFO is empty (i.e., the EMPTY flag goes High). A High on this signal inhibits the counting.

FSTOP is used to stop the FIFO write counter from further counting once the FIFO is full (i.e., the FULL flag goes High). A High on this signal inhibits the counting.

For more information on these signals, refer to the "ESTOP and FSTOP Usage" section on page 2-70.

FULL, EMPTY

When the FIFO is full and no more data can be written, the FULL flag asserts High. The FULL flag is synchronous to WCLK to inhibit writing immediately upon detection of a full condition and to prevent overflows. Since the write address is compared to a resynchronized (and thus time-delayed) version of the read address, the FULL flag will remain asserted until two WCLK active edges after a read operation eliminates the full condition.

When the FIFO is empty and no more data can be read, the EMPTY flag asserts High. The EMPTY flag is synchronous to RCLK to inhibit reading immediately upon detection of an empty condition and to prevent underflows. Since the read address is compared to a resynchronized (and thus time-delayed) version of the write address, the EMPTY flag will remain asserted until two RCLK active edges after a write operation removes the empty condition.

For more information on these signals, refer to the "FIFO Flag Usage Considerations" section on page 2-70.

AFULL, AEMPTY

These are programmable flags and will be asserted on the threshold specified by AFVAL and AEVAL, respectively.

When the number of words stored in the FIFO reaches the amount specified by AEVAL while reading, the AEMPTY output will go High. Likewise, when the number of words stored in the FIFO reaches the amount specified by AFVAL while writing, the AFULL output will go High.

AFVAL, AEVAL

The AEVAL and AFVAL pins are used to specify the almost-empty and almost-full threshold values, respectively. They are 12-bit signals. For more information on these signals, refer to "FIFO Flag Usage Considerations" section.

ESTOP and FSTOP Usage

The ESTOP pin is used to stop the read counter from counting any further once the FIFO is empty (i.e., the EMPTY flag goes High). Likewise, the FSTOP pin is used to stop the write counter from counting any further once the FIFO is full (i.e., the FULL flag goes High).

The FIFO counters in the Fusion device start the count at 0, reach the maximum depth for the configuration (e.g., 511 for a 512×9 configuration), and then restart at 0. An example application for the ESTOP, where the read counter keeps counting, would be writing to the FIFO once and reading the same content over and over without doing another write.

FIFO Flag Usage Considerations

The AEVAL and AFVAL pins are used to specify the 12-bit AEMPTY and AFULL threshold values, respectively. The FIFO contains separate 12-bit write address (WADDR) and read address (RADDR) counters. WADDR is incremented every time a write operation is performed, and RADDR is incremented every time a read operation is performed. Whenever the difference between WADDR and RADDR is greater than or equal to AFVAL, the AFULL output is asserted. Likewise, whenever the difference between WADDR and RADDR is less than or equal to AEVAL, the AEMPTY output is asserted. To handle different read and write aspect ratios, AFVAL and AEVAL are expressed in terms of total data bits instead of total data words. When users specify AFVAL and AEVAL in terms of read or write words, the SmartGen tool translates them into bit addresses and configures these signals automatically. SmartGen configures the AFULL flag to assert when the write address exceeds the read address by at least a predefined value. In a 2k×8 FIFO, for example, a value of 1,500 for AFVAL means that the AFULL flag will be asserted after a write when the difference between the write address and the read address reaches 1,500 (there have been at least 1500 more writes than reads). It will stay asserted until the difference between the write and read addresses drops below 1,500.



Device Architecture

Refer to Table 2-46 on page 2-109 and the "Acquisition Time or Sample Time Control" section on page 2-107

$$t_{sample} = (2 + STC) \times t_{ADCCLK}$$

EQ 20

STC: Sample Time Control value (0–255)

t_{SAMPLE} is the sample time

Table 2-46 • STC Bits Function

Name	Bits	Function
STC	[7:0]	Sample time control

Sample time is computed based on the period of ADCCLK.

Distribution Phase

The second phase is called the distribution phase. During distribution phase, the ADC computes the equivalent digital value from the value stored in the input capacitor. In this phase, the output signal SAMPLE goes back to '0', indicating the sample is completed; but the BUSY signal remains '1', indicating the ADC is still busy for distribution. The distribution time depends strictly on the number of bits. If the ADC is configured as a 10-bit ADC, then 10 ADCCLK cycles are needed. EQ 8 describes the distribution time.

$$t_{distrib} = N \times t_{ADCCLK}$$

EQ 21

N: Number of bits

Post-Calibration Phase

The last phase is the post-calibration phase. This is an optional phase. The post-calibration phase takes two ADCCLK cycles. The output BUSY signal will remain '1' until the post-calibration phase is completed. If the post-calibration phase is skipped, then the BUSY signal goes to '0' after distribution phase. As soon as BUSY signal goes to '0', the DATAVALID signal goes to '1', indicating the digital result is available on the RESULT output signals. DATAVAILD will remain '1' until the next ADCSTART is asserted. Microsemi recommends enabling post-calibration to compensate for drift and temperature-dependent effects. This ensures that the ADC remains consistent over time and with temperature. The post-calibration phase is enabled by bit 3 of the Mode register. EQ 9 describes the post-calibration time.

$$t_{post-cal} = MODE[3] \times (2 \times t_{ADCCLK})$$

EQ 22

EQ 23

MODE[3]: Bit 3 of the Mode register, described in Table 2-41 on page 2-106.

The calculation for the conversion time for the ADC is summarized in EQ 23.

 $t_{conv} = t_{sync_read} + t_{sample} + t_{distrib} + t_{post-cal} + t_{sync_write}$

t_{conv}: conversion time

 t_{sync_read} : maximum time for a signal to synchronize with SYSCLK. For calculation purposes, the worst case is a period of SYSCLK, t_{SYSCLK} .

t_{sample}: Sample time

t_{distrib}: Distribution time

tpost-cal: Post-calibration time

 t_{sync_write} : Maximum time for a signal to synchronize with SYSCLK. For calculation purposes, the worst case is a period of SYSCLK, t_{SYSCLK} .



Typical Performance Characteristics



Temperature Errror vs. Die Temperature





Figure 2-95 • Effect of External Sensor Capacitance



Device Architecture

Table 2-50 • ADC Characteristics in Direct Input Mode (continued)

Commercial Temperature Range Conditions, $T_J = 85^{\circ}C$ (unless noted otherwise), Typical: VCC33A = 3.3 V, VCC = 1.5 V

Parameter	Description	Condition	Min.	Тур.	Max.	Units
Dynamic Pe	erformance					
SNR	Signal-to-Noise Ratio	8-bit mode	48.0	49.5		dB
		10-bit mode	58.0	60.0		dB
		12-bit mode	62.9	64.5		dB
SINAD	Signal-to-Noise Distortion	8-bit mode	47.6	49.5		dB
		10-bit mode	57.4	59.8		dB
		12-bit mode	62.0	64.2		dB
THD	Total Harmonic Distortion	8-bit mode		-74.4	-63.0	dBc
		10-bit mode		-78.3	-63.0	dBc
		12-bit mode		-77.9	-64.4	dBc
ENOB	Effective Number of Bits	8-bit mode	7.6	7.9		bits
		10-bit mode	9.5	9.6		bits
		12-bit mode	10.0	10.4		bits
Conversion	Rate					
	Conversion Time	8-bit mode	1.7			μs
		10-bit mode	1.8			μs
		12-bit mode	2			μs
	Sample Rate	8-bit mode			600	Ksps
		10-bit mode			550	Ksps
		12-bit mode			500	Ksps

Notes:

1. Accuracy of the external reference is 2.56 V \pm 4.6 mV.

2. Data is based on characterization.

3. The sample rate is time-shared among active analog inputs.



Device Architecture

Similarly,

Min. Output Voltage = (Max. Negative input offset) + (Input Voltage x Max. Negative Channel Gain) = $(-88 \text{ mV}) + (5 \text{ V} \times 0.96) = 4.712 \text{ V}$

Calculating Accuracy for a Calibrated Analog Channel

Formula

For a given prescaler range, EQ 31 gives the output voltage.

Output Voltage = Channel Error in V + Input Voltage

EQ 31

where

Channel Error in V = Total Channel Error in LSBs x Equivalent voltage per LSB

Example

Input Voltage = 5 VChosen Prescaler range = 8 V range Refer to Table 2-52 on page 2-123.

Max. Output Voltage = Max. Positive Channel Error in V + Input Voltage Max. Positive Channel Error in V = (6 LSB) × (8 mV per LSB in 10-bit mode) = 48 mV Max. Output Voltage = 48 mV + 5 V = **5.048 V**

Similarly,

Min. Output Voltage = Max. Negative Channel Error in V + Input Voltage = (-48 mV) + 5 V = 4.952 V

Calculating LSBs from a Given Error Budget

Formula

For a given prescaler range, LSB count = ± (Input Voltage × Required % error) / (Equivalent voltage per LSB)

Example

Input Voltage = $3.3 \vee$ Required error margin= 1% Refer to Table 2-52 on page 2-123. Equivalent voltage per LSB = 16 mV for a 16V prescaler, with ADC in 10-bit mode LSB Count = $\pm (5.0 \vee \times 1\%) / (0.016)$ LSB Count = ± 3.125 Equivalent voltage per LSB = 8 mV for an $8 \vee$ prescaler, with ADC in 10-bit mode LSB Count = $\pm (5.0 \vee \times 1\%) / (0.008)$ LSB Count = $\pm (5.0 \vee \times 1\%) / (0.008)$ LSB Count = ± 6.25 The $8 \vee$ prescaler satisfies the calculated LSB count accuracy requirement (see Table 2-52 on page 2-123).

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-90 • Summary of AC Measuring Points Applicable to All I/O Bank Types

Standard	Input Reference Voltage (VREF_TYP)	Board Termination Voltage (VTT_REF)	Measuring Trip Point (Vtrip)
3.3 V LVTTL / 3.3 V LVCMOS	_	-	1.4 V
2.5 V LVCMOS	_	-	1.2 V
1.8 V LVCMOS	-	-	0.90 V
1.5 V LVCMOS	-	-	0.75 V
3.3 V PCI	_	_	0.285 * VCCI (RR) 0.615 * VCCI (FF))
3.3 V PCI-X	-	_	0.285 * VCCI (RR) 0.615 * VCCI (FF)
3.3 V GTL	0.8 V	1.2 V	VREF
2.5 V GTL	0.8 V	1.2 V	VREF
3.3 V GTL+	1.0 V	1.5 V	VREF
2.5 V GTL+	1.0 V	1.5 V	VREF
HSTL (I)	0.75 V	0.75 V	VREF
HSTL (II)	0.75 V	0.75 V	VREF
SSTL2 (I)	1.25 V	1.25 V	VREF
SSTL2 (II)	1.25 V	1.25 V	VREF
SSTL3 (I)	1.5 V	1.485 V	VREF
SSTL3 (II)	1.5 V	1.485 V	VREF
LVDS	-	-	Cross point
LVPECL	-	-	Cross point

Table 2-91 • I/O AC Parameter Definitions

Parameter	Definition
t _{DP}	Data to Pad delay through the Output Buffer
t _{PY}	Pad to Data delay through the Input Buffer with Schmitt trigger disabled
t _{DOUT}	Data to Output Buffer delay through the I/O interface
t _{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t _{DIN}	Input Buffer to Data delay through the I/O interface
t _{PYS}	Pad to Data delay through the Input Buffer with Schmitt trigger enabled
t _{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t _{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t _{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t _{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t _{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t _{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-96 • I/O Output Buffer Maximum Resistances ¹ (continued)

Standard	Drive Strength	R _{PULL-DOWN} (ohms) ²	R _{PULL-UP} (ohms) ³
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA	25	25
SSTL2 (I)	17 mA	27	31
SSTL2 (II)	21 mA	13	15
SSTL3 (I)	16 mA	44	69
SSTL3 (II)	24 mA	18	32
Applicable to Advanced I/O Ba	nks		•
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

 These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCC, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: http://www.microsemi.com/soc/techdocs/models/ibis.html.

2. R_(PULL-DOWN-MAX) = VOLspec / I_{OLspec}

3. R_(PULL-UP-MAX) = (VCCImax – VOHspec) / IOHspec

Microsemi.

Device Architecture

Table 2-130 • 1.5 V LVCMOS Low Slew

Commercial Temperature Range Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V Applicable to Advanced I/Os

Drive	Speed												
Strength	Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	0.66	12.78	0.04	1.31	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	-1	0.56	10.87	0.04	1.11	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	-2	0.49	9.55	0.03	0.98	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.31	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	-1	0.56	8.51	0.04	1.11	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	-2	0.49	7.47	0.03	0.98	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
8 mA	Std.	0.66	9.33	0.04	1.31	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	-1	0.56	7.94	0.04	1.11	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	-2	0.49	6.97	0.03	0.98	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.31	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	-1	0.56	7.58	0.04	1.11	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	-2	0.49	6.65	0.03	0.98	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

Table 2-131 • 1.5 V LVCMOS High Slew

Commercial Temperature Range Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V Applicable to Advanced I/Os

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
2 mA	Std.	0.66	8.36	0.04	1.44	0.43	6.82	8.36	3.39	2.77	9.06	10.60	ns
	-1	0.56	7.11	0.04	1.22	0.36	5.80	7.11	2.88	2.35	7.71	9.02	ns
	-2	0.49	6.24	0.03	1.07	0.32	5.10	6.24	2.53	2.06	6.76	7.91	ns
4 mA	Std.	0.66	5.31	0.04	1.44	0.43	4.85	5.31	3.74	3.40	7.09	7.55	ns
	-1	0.56	4.52	0.04	1.22	0.36	4.13	4.52	3.18	2.89	6.03	6.42	ns
	-2	0.49	3.97	0.03	1.07	0.32	3.62	3.97	2.79	2.54	5.29	5.64	ns
8 mA	Std.	0.66	4.67	0.04	1.44	0.43	4.55	4.67	3.82	3.56	6.78	6.90	ns
	-1	0.56	3.97	0.04	1.22	0.36	3.87	3.97	3.25	3.03	5.77	5.87	ns
	-2	0.49	3.49	0.03	1.07	0.32	3.40	3.49	2.85	2.66	5.07	5.16	ns
12 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	-1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	-2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.



Table 2-174 • Parameter Definitions and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t _{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
tosud	Data Setup Time for the Output Data Register	F, H
t _{OHD}	Data Hold Time for the Output Data Register	F, H
t _{OSUE}	Enable Setup Time for the Output Data Register	G, H
t _{OHE}	Enable Hold Time for the Output Data Register	G, H
t _{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L,DOUT
t _{OREMPRE}	Asynchronous Preset Removal Time for the Output Data Register	L, H
t _{ORECPRE}	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t _{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t _{OESUD}	Data Setup Time for the Output Enable Register	J, H
t _{OEHD}	Data Hold Time for the Output Enable Register	J, H
t _{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t _{OEHE}	Enable Hold Time for the Output Enable Register	K, H
t _{OEPRE2Q}	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
t _{OEREMPRE}	Asynchronous Preset Removal Time for the Output Enable Register	I, H
t _{OERECPRE}	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t _{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t _{ISUD}	Data Setup Time for the Input Data Register	C, A
t _{IHD}	Data Hold Time for the Input Data Register	C, A
t _{ISUE}	Enable Setup Time for the Input Data Register	B, A
t _{IHE}	Enable Hold Time for the Input Data Register	B, A
t _{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
t _{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	D, A
t _{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-137 on page 2-212 for more information.



User-Defined Supply Pins

VREF I/O Voltage Reference

Reference voltage for I/O minibanks. Both AFS600 and AFS1500 (north bank only) support Microsemi Pro I/O. These I/O banks support voltage reference standard I/O. The VREF pins are configured by the user from regular I/Os, and any I/O in a bank, except JTAG I/Os, can be designated as the voltage reference I/O. Only certain I/O standards require a voltage reference—HSTL (I) and (II), SSTL2 (I) and (II), SSTL3 (I) and (II), and GTL/GTL+. One VREF pin can support the number of I/Os available in its minibank.

VAREF Analog Reference Voltage

The Fusion device can be configured to generate a 2.56 V internal reference voltage that can be used by the ADC. While using the internal reference, the reference voltage is output on the VAREF pin for use as a system reference. If a different reference voltage is required, it can be supplied by an external source and applied to this pin. The valid range of values that can be supplied to the ADC is 1.0 V to 3.3 V. When VAREF is internally generated by the Fusion device, a bypass capacitor must be connected from this pin to ground. The value of the bypass capacitor should be between 3.3 µF and 22 µF, which is based on the needs of the individual designs. The choice of the capacitor value has an impact on the settling time it takes the VAREF signal to reach the required specification of 2.56 V to initiate valid conversions by the ADC. If the lower capacitor value is chosen, the settling time required for VAREF to achieve 2.56 V will be shorter than when selecting the larger capacitor value. The above range of capacitor values supports the accuracy specification of the ADC, which is detailed in the datasheet. Designers choosing the smaller capacitor value will not obtain as much margin in the accuracy as that achieved with a larger capacitor value. Depending on the capacitor value selected in the Analog System Builder, a tool in Libero SoC, an automatic delay circuit will be generated using logic tiles available within the FPGA to ensure that VAREF has achieved the 2.56 V value. Microsemi recommends customers use 10 uF as the value of the bypass capacitor. Designers choosing to use an external VAREF need to ensure that a stable and clean VAREF source is supplied to the VAREF pin before initiating conversions by the ADC. Designers should also make sure that the ADCRESET signal is deasserted before initiating valid conversions.²

If the user connects VAREF to external 3.3 V on their board, the internal VAREF driving OpAmp tries to bring the pin down to the nominal 2.56 V until the device is programmed and up/functional. Under this scenario, it is recommended to connect an external 3.3 V supply through a ~1 KOhm resistor to limit current, along with placing a 10-100nF capacitor between VAREF and GNDA.

User Pins

I/O

User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected. Unused I/O pins are configured as inputs with pull-up resistors.

During programming, I/Os become tristated and weakly pulled up to VCCI. With the VCCI and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os get instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

Axy Analog Input/Output

Analog I/O pin, where x is the analog pad type (C = current pad, G = Gate driver pad, T = Temperature pad, V = Voltage pad) and y is the Analog Quad number (0 to 9). There is a minimum 1 M Ω to ground on AV, AC, and AT. This pin can be left floating when it is unused.

^{2.} The ADC is functional with an external reference down to 1V, however to meet the performance parameters highlighted in the datasheet refer to the VAREF specification in Table 3-2 on page 3-3.

Calculating Power Dissipation

Quiescent Supply Current

Table 3-8 • AFS1500 Quiescent Supply Current Characteristics

Parameter	Description	Conditions	Temp.	Min.	Тур.	Max.	Unit
ICC ¹	1.5 V quiescent current	Operational standby ⁴ ,	T _J = 25°C		20	40	mA
		VCC = 1.575 V	T _J = 85°C		32	65	mA
			T _J = 100°C		59	120	mA
		Standby mode ⁵ or Sleep mode ⁶ , VCC = 0 V			0	0	μA
ICC33 ²	3.3 V analog supplies	Operational standby ⁴ ,	T _J = 25°C		9.8	13	mA
	current	VCC33 = 3.63 V	T _J = 85°C		10.7	14	mA
			T _J = 100°C		10.8	15	mA
		Operational standby, only Analog Quad and –3.3 V output ON, VCC33 = 3.63 V	T _J = 25°C		0.31	2	mA
			T _J = 85°C		0.35	2	mA
			T _J = 100°C		0.45	2	mA
		Standby mode ⁵ , VCC33 = 3.63 V	T _J = 25°C		2.9	3.6	mA
			T _J = 85°C		2.9	4	mA
			T _J = 100°C		3.3	6	mA
		Sleep mode ⁶ , VCC33 = 3.63 V	T _J = 25°C		17	19	μA
			T _J = 85°C		18	20	μA
			T _J = 100°C		24	25	μA
ICCI ³	I/O quiescent current	Operational standby ⁴ ,	T _J = 25°C		417	649	μA
		Standby mode, and Sleep Mode ^o , VCCIx = 3.63 V	T _J = 85°C		417	649	μA
			T _J = 100°C		417	649	μA

Notes:

1. ICC is the 1.5 V power supplies, ICC and ICC15A.

2. ICC33A includes ICC33A, ICC33PMP, and ICCOSC.

3. ICCI includes all ICCI0, ICCI1, ICCI2, and ICCI4.

4. Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.

5. XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.

6. Sleep Mode, VCC = VJTAG = VPUMP = 0 V.



Package Pin Assignments

	FG484		FG484				
Pin Number	AFS600 Function	AFS1500 Function	Pin Number	AFS600 Function	AFS1500 Function		
E9	NC	IO08PDB0V1	F22	IO35PDB2V0	IO51PDB2V0		
E10	GND	GND	G1	IO77PDB4V0	IO115PDB4V0		
E11	IO15NDB1V0	IO22NDB1V0	G2	GND	GND		
E12	IO15PDB1V0	IO22PDB1V0	G3	IO78NDB4V0	IO116NDB4V0		
E13	GND	GND	G4	IO78PDB4V0	IO116PDB4V0		
E14	NC	IO32PPB1V1	G5	VCCIB4	VCCIB4		
E15	NC	IO36NPB1V2	G6	NC	IO117PDB4V0		
E16	VCCIB1	VCCIB1	G7	VCCIB4	VCCIB4		
E17	GND	GND	G8	GND	GND		
E18	NC	IO47NPB2V0	G9	IO04NDB0V0	IO06NDB0V1		
E19	IO33PDB2V0	IO49PDB2V0	G10	IO04PDB0V0	IO06PDB0V1		
E20	VCCIB2	VCCIB2	G11	IO12NDB0V1	IO16NDB0V2		
E21	IO32NDB2V0	IO46NDB2V0	G12	IO12PDB0V1	IO16PDB0V2		
E22	GBC2/IO32PDB2V0	GBC2/IO46PDB2V0	G13	NC	IO28NDB1V1		
F1	IO80NDB4V0	IO118NDB4V0	G14	NC	IO28PDB1V1		
F2	IO80PDB4V0	IO118PDB4V0	G15	GND	GND		
F3	NC	IO119NSB4V0	G16	NC	IO38PPB1V2		
F4	IO84NDB4V0	IO124NDB4V0	G17	NC	IO53PDB2V0		
F5	GND	GND	G18	VCCIB2	VCCIB2		
F6	VCOMPLA	VCOMPLA	G19	IO36PDB2V0	IO52PDB2V0		
F7	VCCPLA	VCCPLA	G20	IO36NDB2V0	IO52NDB2V0		
F8	VCCIB0	VCCIB0	G21	GND	GND		
F9	IO08NDB0V1	IO12NDB0V1	G22	IO35NDB2V0	IO51NDB2V0		
F10	IO08PDB0V1	IO12PDB0V1	H1	IO77NDB4V0	IO115NDB4V0		
F11	VCCIB0	VCCIB0	H2	IO76PDB4V0	IO113PDB4V0		
F12	VCCIB1	VCCIB1	H3	VCCIB4	VCCIB4		
F13	IO22NDB1V0	IO30NDB1V1	H4	IO79NDB4V0	IO114NDB4V0		
F14	IO22PDB1V0	IO30PDB1V1	H5	IO79PDB4V0	IO114PDB4V0		
F15	VCCIB1	VCCIB1	H6	NC	IO117NDB4V0		
F16	NC	IO36PPB1V2	H7	GND	GND		
F17	NC	IO38NPB1V2	H8	VCC	VCC		
F18	GND	GND	H9	VCCIB0	VCCIB0		
F19	IO33NDB2V0	IO49NDB2V0	H10	GND	GND		
F20	IO34PDB2V0	IO50PDB2V0	H11	VCCIB0	VCCIB0		
F21	IO34NDB2V0	IO50NDB2V0	H12	VCCIB1	VCCIB1		

	FG484			FG484	
Pin Number	AFS600 Function	AFS1500 Function	Pin Number	AFS600 Function	AFS1500 Function
H13	GND	GND	K4	IO75NDB4V0	IO110NDB4V0
H14	VCCIB1	VCCIB1	K5	GND	GND
H15	GND	GND	K6	NC	IO104NDB4V0
H16	GND	GND	K7	NC	IO111NDB4V0
H17	NC	IO53NDB2V0	K8	GND	GND
H18	IO38PDB2V0	IO57PDB2V0	K9	VCC	VCC
H19	GCA2/IO39PDB2V0	GCA2/IO59PDB2V0	K10	GND	GND
H20	VCCIB2	VCCIB2	K11	VCC	VCC
H21	IO37NDB2V0	IO54NDB2V0	K12	GND	GND
H22	IO37PDB2V0	IO54PDB2V0	K13	VCC	VCC
J1	NC	IO112PPB4V0	K14	GND	GND
J2	IO76NDB4V0	IO113NDB4V0	K15	GND	GND
J3	GFB2/IO74PDB4V0	GFB2/IO109PDB4V0	K16	IO40NDB2V0	IO60NDB2V0
J4	GFA2/IO75PDB4V0	GFA2/IO110PDB4V0	K17	NC	IO58PDB2V0
J5	NC	IO112NPB4V0	K18	GND	GND
J6	NC	IO104PDB4V0	K19	NC	IO68NPB2V0
J7	NC	IO111PDB4V0	K20	IO41NDB2V0	IO61NDB2V0
J8	VCCIB4	VCCIB4	K21	GND	GND
J9	GND	GND	K22	IO42NDB2V0	IO56NDB2V0
J10	VCC	VCC	L1	IO73NDB4V0	IO108NDB4V0
J11	GND	GND	L2	VCCOSC	VCCOSC
J12	VCC	VCC	L3	VCCIB4	VCCIB4
J13	GND	GND	L4	XTAL2	XTAL2
J14	VCC	VCC	L5	GFC1/IO72PDB4V0	GFC1/IO107PDB4V0
J15	VCCIB2	VCCIB2	L6	VCCIB4	VCCIB4
J16	GCB2/IO40PDB2V0	GCB2/IO60PDB2V0	L7	GFB1/IO71PDB4V0	GFB1/IO106PDB4V0
J17	NC	IO58NDB2V0	L8	VCCIB4	VCCIB4
J18	IO38NDB2V0	IO57NDB2V0	L9	GND	GND
J19	IO39NDB2V0	IO59NDB2V0	L10	VCC	VCC
J20	GCC2/IO41PDB2V0	GCC2/IO61PDB2V0	L11	GND	GND
J21	NC	IO55PSB2V0	L12	VCC	VCC
J22	IO42PDB2V0	IO56PDB2V0	L13	GND	GND
K1	GFC2/IO73PDB4V0	GFC2/IO108PDB4V0	L14	VCC	VCC
K2	GND	GND	L15	VCCIB2	VCCIB2
K3	IO74NDB4V0	IO109NDB4V0	L16	IO48PDB2V0	IO70PDB2V0



Package Pin Assignments

FG484			FG484			
Pin Number	AFS600 Function	AFS1500 Function	Pin Number	AFS600 Function	AFS1500 Function	
L17	VCCIB2	VCCIB2	N8	GND	GND	
L18	IO46PDB2V0	IO69PDB2V0	N9	GND	GND	
L19	GCA1/IO45PDB2V0	GCA1/IO64PDB2V0	N10	VCC	VCC	
L20	VCCIB2	VCCIB2	N11	GND	GND	
L21	GCC0/IO43NDB2V0	GCC0/IO62NDB2V0	N12	VCC	VCC	
L22	GCC1/IO43PDB2V0	GCC1/IO62PDB2V0	N13	GND	GND	
M1	NC	IO103PDB4V0	N14	VCC	VCC	
M2	XTAL1	XTAL1	N15	GND	GND	
M3	VCCIB4	VCCIB4	N16	GDB2/IO56PDB2V0	GDB2/IO83PDB2V0	
M4	GNDOSC	GNDOSC	N17	NC	IO78PDB2V0	
M5	GFC0/IO72NDB4V0	GFC0/IO107NDB4V0	N18	GND	GND	
M6	VCCIB4	VCCIB4	N19	IO47NDB2V0	IO72NDB2V0	
M7	GFB0/IO71NDB4V0	GFB0/IO106NDB4V0	N20	IO47PDB2V0	IO72PDB2V0	
M8	VCCIB4	VCCIB4	N21	GND	GND	
M9	VCC	VCC	N22	IO49PDB2V0	IO71PDB2V0	
M10	GND	GND	P1	GFA1/IO70PDB4V0	GFA1/IO105PDB4V0	
M11	VCC	VCC	P2	GFA0/IO70NDB4V0	GFA0/IO105NDB4V0	
M12	GND	GND	P3	IO68NDB4V0	IO101NDB4V0	
M13	VCC	VCC	P4	IO65PDB4V0	IO96PDB4V0	
M14	GND	GND	P5	IO65NDB4V0	IO96NDB4V0	
M15	VCCIB2	VCCIB2	P6	NC	IO99NDB4V0	
M16	IO48NDB2V0	IO70NDB2V0	P7	NC	IO97NDB4V0	
M17	VCCIB2	VCCIB2	P8	VCCIB4	VCCIB4	
M18	IO46NDB2V0	IO69NDB2V0	P9	VCC	VCC	
M19	GCA0/IO45NDB2V0	GCA0/IO64NDB2V0	P10	GND	GND	
M20	VCCIB2	VCCIB2	P11	VCC	VCC	
M21	GCB0/IO44NDB2V0	GCB0/IO63NDB2V0	P12	GND	GND	
M22	GCB1/IO44PDB2V0	GCB1/IO63PDB2V0	P13	VCC	VCC	
N1	NC	IO103NDB4V0	P14	GND	GND	
N2	GND	GND	P15	VCCIB2	VCCIB2	
N3	IO68PDB4V0	IO101PDB4V0	P16	IO56NDB2V0	IO83NDB2V0	
N4	NC	IO100NPB4V0	P17	NC	IO78NDB2V0	
N5	GND	GND	P18	GDA1/IO54PDB2V0	GDA1/IO81PDB2V0	
N6	NC	IO99PDB4V0	P19	GDB1/IO53PDB2V0	GDB1/IO80PDB2V0	
N7	NC	IO97PDB4V0	P20	IO51NDB2V0	IO73NDB2V0	

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FG676		FG676		FG676	
Pin Number	AFS1500 Function	Pin Number	AFS1500 Function	Pin Number	AFS1500 Function
R21	IO72NDB2V0	U5	VCCIB4	V15	AC5
R22	IO72PDB2V0	U6	IO91PDB4V0	V16	NC
R23	GND	U7	IO91NDB4V0	V17	GNDA
R24	IO71PDB2V0	U8	IO92PDB4V0	V18	IO77PPB2V0
R25	VCCIB2	U9	GND	V19	IO74PDB2V0
R26	IO67NDB2V0	U10	GND	V20	VCCIB2
T1	GND	U11	VCC33A	V21	IO82NDB2V0
T2	NC	U12	GNDA	V22	GDA2/IO82PDB2V0
Т3	GFA1/IO105PDB4V0	U13	VCC33A	V23	GND
T4	GFA0/IO105NDB4V0	U14	GNDA	V24	GDC1/IO79PDB2V0
T5	IO101NDB4V0	U15	VCC33A	V25	VCCIB2
Т6	IO96PDB4V0	U16	GNDA	V26	NC
T7	IO96NDB4V0	U17	VCC	W1	GND
Т8	IO99NDB4V0	U18	GND	W2	IO94PPB4V0
Т9	IO97NDB4V0	U19	IO74NDB2V0	W3	IO98PDB4V0
T10	VCCIB4	U20	GDA0/IO81NDB2V0	W4	IO98NDB4V0
T11	VCC	U21	GDB0/IO80NDB2V0	W5	GEC1/IO90PDB4V0
T12	GND	U22	VCCIB2	W6	GEC0/IO90NDB4V0
T13	VCC	U23	IO75NDB2V0	W7	GND
T14	GND	U24	IO75PDB2V0	W8	VCCNVM
T15	VCC	U25	NC	W9	VCCIB4
T16	GND	U26	NC	W10	VCC15A
T17	VCCIB2	V1	NC	W11	GNDA
T18	IO83NDB2V0	V2	VCCIB4	W12	AC4
T19	IO78NDB2V0	V3	IO100PPB4V0	W13	VCC33A
T20	GDA1/IO81PDB2V0	V4	GND	W14	GNDA
T21	GDB1/IO80PDB2V0	V5	IO95PDB4V0	W15	AG5
T22	IO73NDB2V0	V6	IO95NDB4V0	W16	GNDA
T23	IO73PDB2V0	V7	VCCIB4	W17	PUB
T24	IO71NDB2V0	V8	IO92NDB4V0	W18	VCCIB2
T25	NC	V9	GNDNVM	W19	TDI
T26	GND	V10	GNDA	W20	GND
U1	NC	V11	NC	W21	IO84NDB2V0
U2	NC	V12	AV4	W22	GDC2/IO84PDB2V0
U3	IO102PDB4V0	V13	NC	W23	IO77NPB2V0
U4	IO102NDB4V0	V14	AV5	W24	GDC0/IO79NDB2V0

Revision	Changes	Page
Revision 2 (continued)	The prescalar range for the 'Analog Input (direct input to ADC)" configurations was removed as inapplicable for direct inputs. The input resistance for direct inputs is covered in Table 2-50 • ADC Characteristics in Direct Input Mode (SAR 31201).	2-120
	The "Examples" for calibrating accuracy for ADC channels were revised and corrected to make them consistent with terminology in the associated tables (SARs 36791, 36773).	2-124
	A note was added to Table 2-56 • Analog Quad ACM Byte Assignment and the introductory text for Table 2-66 • Internal Temperature Monitor Control Truth Table, stating that for the internal temperature monitor to function, Bit 0 of Byte 2 for all 10 Quads must be set (SAR 34418).	2-129, 2-131
	t_{DOUT} was corrected to t_{DIN} in Figure 2-116 \bullet Input Buffer Timing Model and Delays (example) (SAR 37115).	2-161
	The formulas in the table notes for Table 2-97 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34751).	2-171
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34877).	2-175
	The following notes were removed from Table 2-168 • Minimum and Maximum DC Input and Output Levels (SAR 34808): ±5%	2-209
	Differential input voltage = ±350 mV	
	An incomplete, duplicate sentence was removed from the end of the "GNDAQ Ground (analog quiet)" pin description (SAR 30185).	2-223
	Information about configuration of unused I/Os was added to the "User Pins" section (SAR 32642).	2-225
	The following information was added to the pin description for "XTAL1 Crystal Oscillator Circuit Input" and "XTAL2 Crystal Oscillator Circuit Input" (SAR 24119).	2-227
	The input resistance to ground value in Table 3-3 • Input Resistance of Analog Pads for Analog Input (direct input to ADC), was corrected from 1 M Ω (typical) to 2 k Ω (typical) (SAR 34371).	3-4
	The Storage Temperature column in Table 3-5 • FPGA Programming, Storage, and Operating Limits stated Min. T_J twice for commercial and industrial product grades and has been corrected to Min. T_J and Max. T_J (SAR 29416).	3-5
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Dynamic Contribution—PCLOCK" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the <i>Fusion FPGA Fabric User's Guide</i> (SAR 34741).	3-24
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 36612).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "Fusion Device Status" table indicates the status for each device in the device family.	N/A

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Revision	Changes	Page
Advance v0.6 (continued)	The "Analog-to-Digital Converter Block" section was updated with the following statement: "All results are MSB justified in the ADC."	2-99
	The information about the ADCSTART signal was updated in the "ADC Description" section.	2-102
	Table 2-46 · Analog Channel Specifications was updated.	2-118
	Table 2-47 · ADC Characteristics in Direct Input Mode was updated.	2-121
	Table 2-51 • ACM Address Decode Table for Analog Quad was updated.	2-127
	In Table 2-53 • Analog Quad ACM Byte Assignment, the Function and Default Setting for Bit 6 in Byte 3 was updated.	2-130
	The "Introduction" section was updated to include information about digital inputs, outputs, and bibufs.	2-133
	In Table 2-69 • Fusion Pro I/O Features, the programmable delay descriptions were updated for the following features:	2-137
	Single-ended receiver	
	Voltage-referenced differential receiver	
	The "liker I/O Naming Convention" section was undeted to include "V/" and "r"	2 150
	descriptions	2-159
	The "VCC33PMP Analog Power Supply (3.3 V)" section was updated to include information about avoiding high current draw.	2-224
	The "VCCNVM Flash Memory Block Power Supply (1.5 V)" section was updated to include information about avoiding high current draw.	2-224
	The "VMVx I/O Supply Voltage (quiet)" section was updated to include this statement: VMV and VCCI must be connected to the same power supply and V_{CCI} pins within a given I/O bank.	2-185
	The "PUB Push Button" section was updated to include information about leaving the pin floating if it is not used.	2-228
	The "PTBASE Pass Transistor Base" section was updated to include information about leaving the pin floating if it is not used.	2-228
	The "PTEM Pass Transistor Emitter" section was updated to include information about leaving the pin floating if it is not used.	2-228
	The heading was incorrect in the "208-Pin PQFP" table. It should be AFS250 and not AFS090.	3-8



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